

TLP155

1. Applications

- Plasma Display Panels (PDPs)
- Transistor Inverters
- MOSFET Gate Drivers
- IGBT Gate Drivers

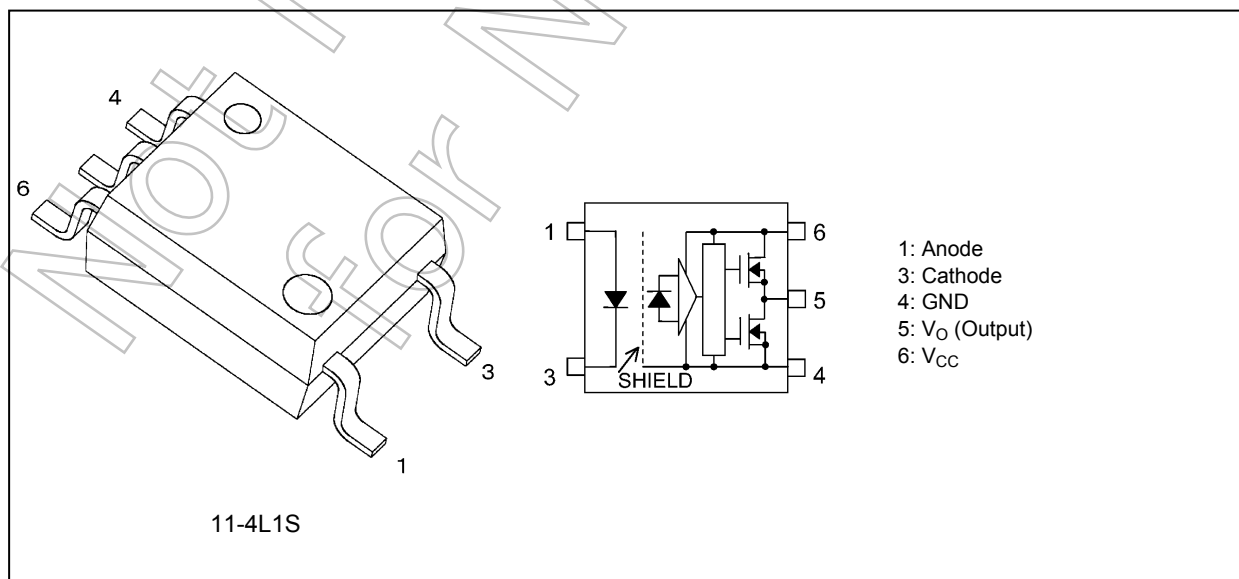
2. General

The Toshiba TLP155 consists of a GaAs infrared light-emitting diodes and integrated high gain, high-speed photodetectors. The TLP155 is housed in the SO6 package. The photodetector has an internal Faraday shield that provides a guaranteed Common-mode transient immunity of ± 20 kV/ μ s. TLP155 is suitable for direct gate driving circuit for IGBTs or power MOSFETs.

3. Features

- (1) Buffer logic type (Totem pole output)
 - (2) Package:SO6
 - (3) Output peak current: ± 0.6 A (max)
 - (4) Operating temperature: -40 to 100 °C
 - (5) Threshold input current: 7.5 mA (max)
 - (6) Propagation delay time: 200 ns (max)
 - (7) Common-mode transient immunity: ± 20 kV/ μ s (min)
 - (8) Propagation delay skew: ± 85 ns(max)
 - (9) Isolation voltage: 3750 Vrms (min)
 - (10) Safety standards
 - UL-approved: UL1577, File No.E67349
 - cUL-approved: CSA Component Acceptance Service No.5A File No.E67349
 - VDE-approved: EN60747-5-5 (**Note 1**)
- Note 1: When an EN60747-5-5 approved type is needed, please designate the **Option (V4)**.

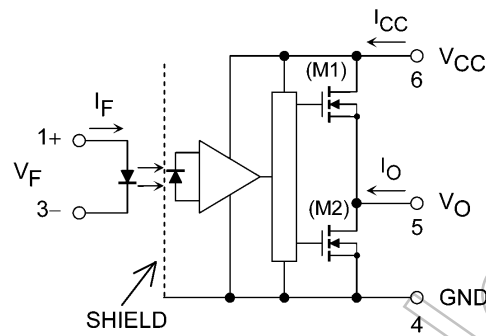
4. Packaging and Pin Assignment



Start of commercial production

2011-09

5. Internal Circuit (Note)



Note: A 0.1- μ F bypass capacitor must be connected between pin 6 and pin 4.

6. Principle of Operation

6.1. Truth Table

Input	LED	M1	M2	Output
H	ON	ON	OFF	H
L	OFF	OFF	ON	L

6.2. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	5.0	mm
Clearance distances	5.0	
Internal isolation thickness	0.4	

7. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

	Characteristics	Symbol	Note	Rating	Unit
LED	Input forward current	I_F		20	mA
	Input forward current derating ($T_a \geq 92\text{ }^\circ\text{C}$)	$\Delta I_F/\Delta T_a$		-0.63	mA/ $^\circ\text{C}$
	Peak transient input forward current	I_{FPT}	(Note 1)	1	A
	Input reverse voltage	V_R		5	V
	Input power dissipation	P_D		40	mW
	Input power dissipation derating ($T_a \geq 92\text{ }^\circ\text{C}$)	$\Delta P_D/\Delta T_a$		-1.2	mW/ $^\circ\text{C}$
	Junction temperature	T_j		125	$^\circ\text{C}$
Detector	Peak high-level output current ($T_a = -40$ to $100\text{ }^\circ\text{C}$)	I_{OPH}	(Note 2)	-0.6	A
	Peak low-level output current ($T_a = -40$ to $100\text{ }^\circ\text{C}$)	I_{OPL}		+0.6	
	Output voltage	V_O		35	V
	Supply voltage	V_{CC}		35	
	Output power dissipation	P_O		80	mW
	Output power dissipation derating ($T_a \geq 85\text{ }^\circ\text{C}$)	$\Delta P_O/\Delta T_a$		-2.0	mW/ $^\circ\text{C}$
	Junction temperature	T_j		125	$^\circ\text{C}$
Common	Operating temperature	T_{opr}		-40 to 100	$^\circ\text{C}$
	Storage temperature	T_{stg}		-55 to 125	
	Lead soldering temperature (10 s)	T_{sol}		260	
	Isolation voltage AC, 60 s, R.H. $\leq 60\%$	BV_S	(Note 3)	3750	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) $\leq 1\text{ }\mu\text{s}$, 300 pps

Note 2: Exponential waveform. Pulse width $\leq 2\text{ }\mu\text{s}$, $f \leq 10\text{ kHz}$, $V_{CC} = 20\text{V}$, $T_a = -40$ to $100\text{ }^\circ\text{C}$

Note 3: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

8. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Typ.	Max	Unit
Threshold input current (L/H)	I_{FLH}	(Note 1)	10	—	15	mA
Threshold input voltage (H/L)	V_{FHL}		0	—	0.8	V
Supply voltage	V_{CC}	(Note 2)	10	—	30	
Peak high-level output current	I_{OPH}		—	—	-0.2	A
Peak low-level output current	I_{OPL}		—	—	+0.2	
Operating temperature	T_{opr}		-40	—	100	°C
Operating frequency	f	(Note 3)	—	—	250	kHz

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this datasheet should also be considered.

Note: A ceramic capacitor (0.1 μ F) should be connected between pin 6 and pin 4 to stabilize the operation of a high-gain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: The rise and fall times of the input on-current should be less than 0.5 μ s.

Note 2: Denotes the operating range, not the recommended operating condition.

Note 3: Exponential waveform. $I_{OPH} \geq -0.25$ A (≤ 80 ns), $I_{OPL} \leq 0.25$ A (≤ 80 ns), $T_a = 100$ °C

**9. Electrical Characteristics (Note)
(Unless otherwise specified, $T_a = -40$ to 100 °C)**

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input forward voltage	V_F		—	$I_F = 10$ mA, $T_a = 25$ °C	1.40	1.57	1.80	V
Input forward voltage temperature coefficient	$\Delta V_F / \Delta T_a$		—	$I_F = 10$ mA	—	-1.8	—	mV/°C
Input reverse current	I_R		—	$V_R = 5$ V, $T_a = 25$ °C	—	—	10	μ A
Input capacitance	C_t		—	$V = 0$ V, $f = 1$ MHz, $T_a = 25$ °C	—	60	—	pF
Peak high-level output current	I_{OPH}	(Note 1)	Fig. 12.1.1	$I_F = 10$ mA, $V_{CC} = 15$ V, $V_{6-5} = 4$ V	—	-0.5	-0.2	A
				$I_F = 10$ mA, $V_{CC} = 15$ V, $V_{6-5} = 10$ V	—	—	-0.4	
Peak low-level output current	I_{OPL}	(Note 1)	Fig. 12.1.2	$I_F = 0$ mA, $V_{CC} = 15$ V, $V_{5-4} = 2$ V	0.2	0.5	—	
				$I_F = 0$ mA, $V_{CC} = 15$ V, $V_{5-4} = 10$ V	0.4	—	—	
High-level output voltage	V_{OH}		Fig. 12.1.3	$I_F = 10$ mA, $V_{CC} = 10$ V, $I_O = -100$ mA	6.0	8.4	—	V
Low-level output voltage	V_{OL}		Fig. 12.1.4	$V_F = 0.8$ V, $V_{CC} = 10$ V, $I_O = 100$ mA	—	0.3	1.0	
High-level supply current	I_{CCH}		Fig. 12.1.5	$I_F = 10$ mA, $V_{CC} = 10$ to 30 V, $V_O = \text{Open}$	—	1.5	3.0	mA
Low-level supply current	I_{CCL}		Fig. 12.1.6	$I_F = 0$ mA, $V_{CC} = 10$ to 30 V, $V_O = \text{Open}$	—	1.5	3.0	
Threshold input current (L/H)	I_{FLH}		—	$V_{CC} = 15$ V, $V_O > 1$ V	—	1.0	7.5	
Threshold input voltage (H/L)	V_{FHL}		—	$V_{CC} = 15$ V, $V_O < 1$ V	0.8	—	—	V
Supply voltage	V_{CC}		—	—	10	—	30	

Note: All typical values are at $T_a = 25$ °C.

Note: This device is designed for low power consumption, making it more sensitive to ESD than its predecessors. Extra care should be taken in the design of circuitry and pc board implementation to avoid ESD problems.

Note 1: I_O application time ≤ 50 μ s, single pulse.

10. Isolation Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

Characteristics	Symbol	Note	Test Conditions	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	(Note 1)	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	—	0.8	—	pF
Isolation resistance	R_S	(Note 1)	$V_S = 500\text{ V}$, R.H. $\leq 60\%$	1×10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	(Note 1)	AC, 60 s	3750	—	—	Vrms
			AC, 1 s in oil	—	10000	—	
			DC, 60 s in oil	—	10000	—	Vdc

Note 1: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

**11. Switching Characteristics (Note)
(Unless otherwise specified, $T_a = -40\text{ to }100\text{ }^\circ\text{C}$)**

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Propagation delay time (L/H)	t_{pLH}	(Note 1)	Fig. 12.1.7	$I_F = 0 \rightarrow 10\text{ mA}$, $V_{CC} = 20\text{ V}$, $R_g = 30\ \Omega$, $C_g = 1\text{ nF}$, $T_a = 25\text{ }^\circ\text{C}$	—	120	170	ns
Propagation delay time (H/L)	t_{pHL}	(Note 1)		$I_F = 10 \rightarrow 0\text{ mA}$, $V_{CC} = 20\text{ V}$, $R_g = 30\ \Omega$, $C_g = 1\text{ nF}$, $T_a = 25\text{ }^\circ\text{C}$	—	120	170	
Propagation delay time (L/H)	t_{pLH}	(Note 1)		$I_F = 0 \rightarrow 10\text{ mA}$, $V_{CC} = 20\text{ V}$, $R_g = 30\ \Omega$, $C_g = 1\text{ nF}$	50	120	200	
Propagation delay time (H/L)	t_{pHL}	(Note 1)		$I_F = 10 \rightarrow 0\text{ mA}$, $V_{CC} = 20\text{ V}$, $R_g = 30\ \Omega$, $C_g = 1\text{ nF}$	50	120	200	
Propagation delay skew (device to device)	t_{psk}	(Note 1) (Note 4)		$I_F = 0 \leftrightarrow 10\text{ mA}$, $V_{CC} = 20\text{ V}$, $R_g = 30\ \Omega$, $C_g = 1\text{ nF}$	-85	—	85	
Pulse width distortion	$ t_{pHL} - t_{pLH} $	(Note 1)		$I_F = 0 \leftrightarrow 10\text{ mA}$, $V_{CC} = 20\text{ V}$, $R_g = 30\ \Omega$, $C_g = 1\text{ nF}$	—	5	50	
Rise time	t_r	(Note 1)		$I_F = 0 \rightarrow 10\text{ mA}$, $V_{CC} = 20\text{ V}$, $R_g = 30\ \Omega$, $C_g = 1\text{ nF}$	—	35	—	
Fall time	t_f	(Note 1)		$I_F = 10 \rightarrow 0\text{ mA}$, $V_{CC} = 20\text{ V}$, $R_g = 30\ \Omega$, $C_g = 1\text{ nF}$	—	15	—	
Common-mode transient immunity at output high	CM_H	(Note 2)	Fig. 12.1.8	$V_{CM} = 1000\text{ V}_{p-p}$, $I_F = 10\text{ mA}$, $V_{CC} = 20\text{ V}$, $T_a = 25\text{ }^\circ\text{C}$, $V_{O(min)} = 16\text{ V}$	± 20	—	—	kV/ μs
Common-mode transient immunity at output low	CM_L	(Note 3)		$V_{CM} = 1000\text{ V}_{p-p}$, $I_F = 0\text{ mA}$, $V_{CC} = 20\text{ V}$, $T_a = 25\text{ }^\circ\text{C}$, $V_{O(max)} = 1\text{ V}$	± 20	—	—	

Note: All typical values are at $T_a = 25\text{ }^\circ\text{C}$.

Note 1: Input signal ($f = 250\text{ kHz}$, duty = 50%, $t_r = t_f = 5\text{ ns}$ or less).

CL is approximately 15 pF which includes probe and stray wiring capacitance.

Note 2: CM_H is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state ($V_O > 16\text{ V}$).

Note 3: CM_L is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_O < 1\text{ V}$).

Note 4: The propagation delay skew, t_{psk} , is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).

12. Test Circuits and Characteristics Curves

12.1. Test Circuits

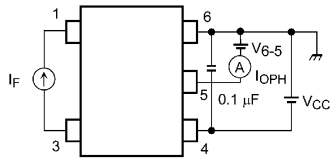


Fig. 12.1.1 IO_{PH} Test Circuit

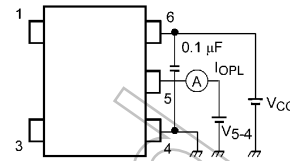
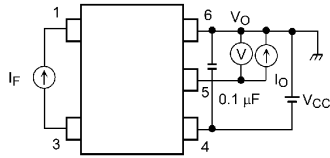


Fig. 12.1.2 IO_{PL} Test Circuit



$V_{OH} = V_{CC} - V_o$

Fig. 12.1.3 VO_H Test Circuit

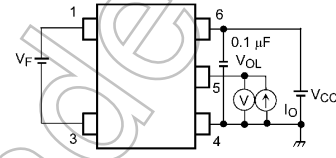


Fig. 12.1.4 VO_L Test Circuit

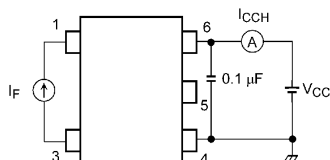


Fig. 12.1.5 IC_{CH} Test Circuit

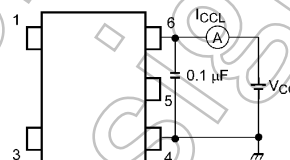
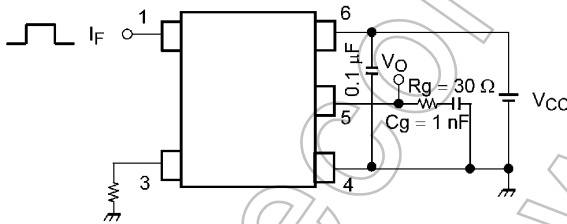


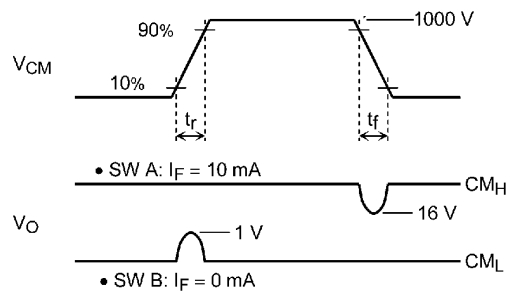
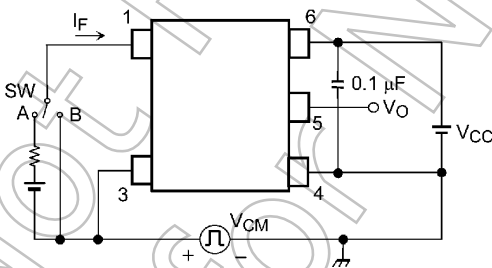
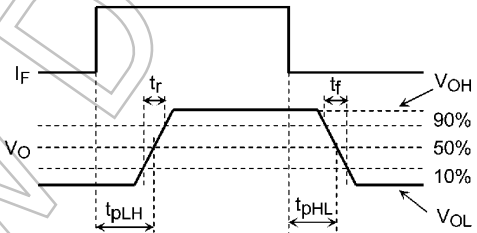
Fig. 12.1.6 IC_{CL} Test Circuit

$I_F = 10 \text{ mA (P.G.)}$
 $(f = 250 \text{ kHz, duty} = 50\%, t_r = t_f = 5 \text{ ns})$



P.G. : Pulse generator

Fig. 12.1.7 Switching Time Test Circuit and Waveform



$CM_L = \frac{800 \text{ V}}{t_r (\mu\text{s})}$

$CM_H = -\frac{800 \text{ V}}{t_f (\mu\text{s})}$

Fig. 12.1.8 Common-Mode Transient Immunity Test Circuit and Waveform

13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

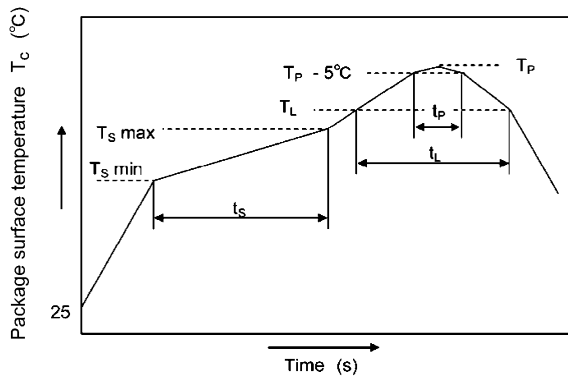
- When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	T_s	150	200	°C
Preheat time	t_s	60	120	s
Ramp-up rate (T_L to T_P)			3	°C/s
Liquidus temperature	T_L	217		°C
Time above T_L	t_L	60	150	s
Peak temperature	T_P	260		°C
Time during which T_c is between ($T_P - 5$) and T_P	t_p	30		s
Ramp-down rate (T_P to T_L)			6	°C/s

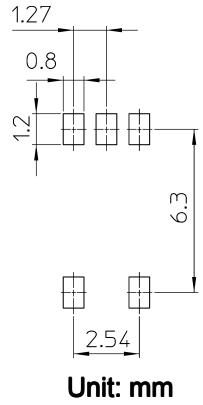
An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

- When using soldering flow
Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
Mounting condition of 260 °C within 10 seconds is recommended.
Flow soldering must be performed once.
- When using soldering Iron
Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C
Heating by soldering iron must be done only once per lead.

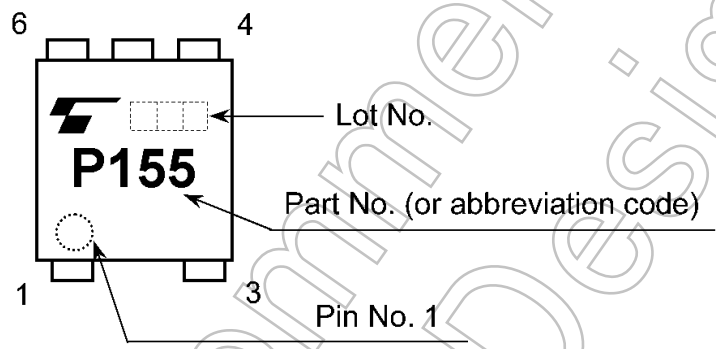
13.2. Precautions for General Storage

- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

14. Land Pattern Dimensions for Reference Only



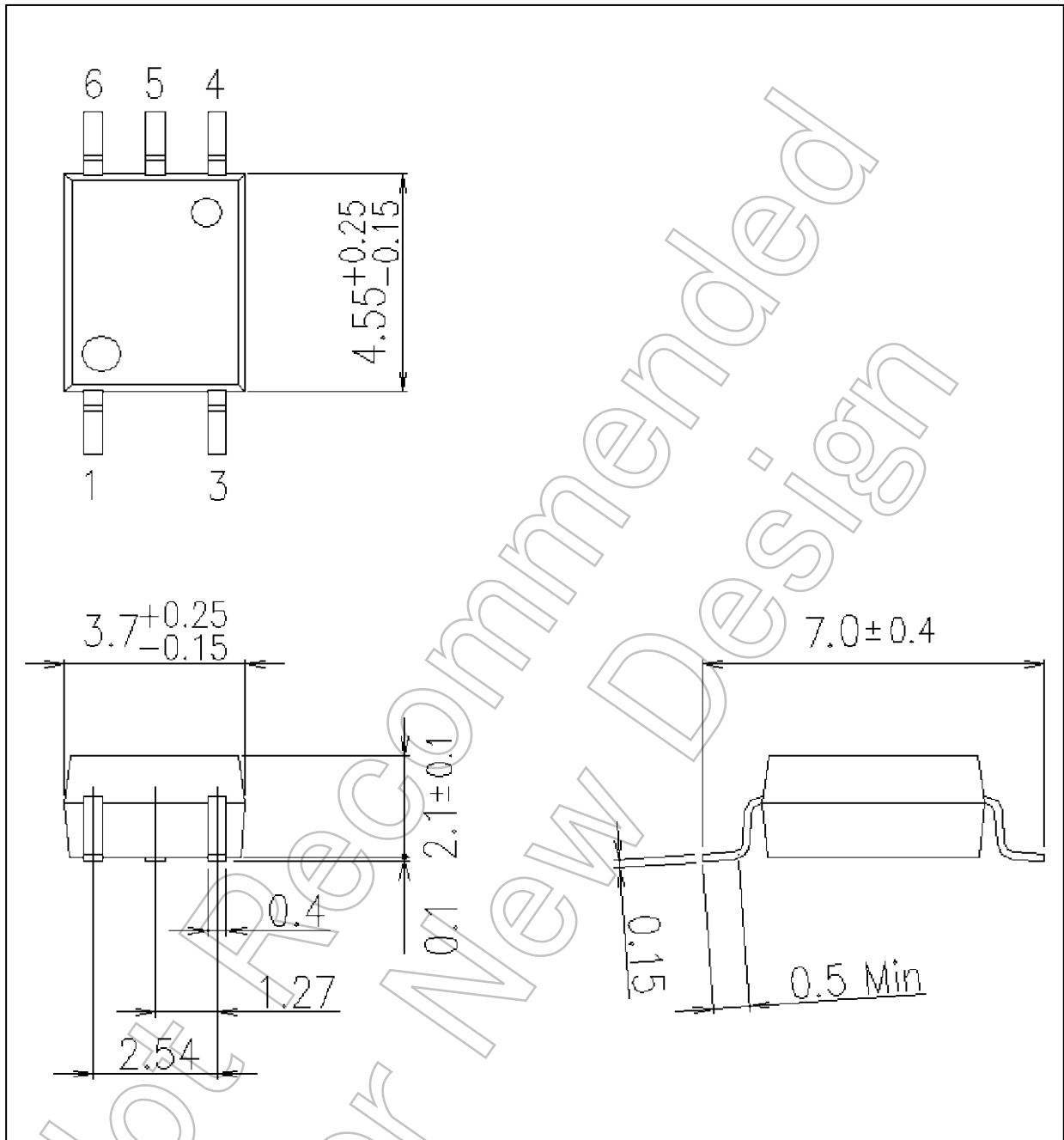
15. Marking



Not Recommended for New Design

Package Dimensions

Unit: mm



Weight: 0.08 g (typ.)

Package Name(s)
TOSHIBA: 11-4L1S

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